| | Type | Hits | Search Text | DBs |
|---|---|---|---|---|
| 1 | IS&R | 15 | (("5008212") or ("5021121") or ("5102815") or ("5242532") or ("5242536") or ("5312717") or ("5441596") or ("5451290") or ("5474648") or ("5662770") or ("5843226") or ("5998302") or ("6083844") or ("6159794") or ("6162696")).PN. | USPAT |
| 2 | IS&R | 1999 | (438/629,636,637,639,640).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 3 | BRS | 1 | substrate with ((Si silicon) and (Ge germanium) and (gallium adj nitride gan "GaN" "Ga N")) and DRAM and oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 4 | BRS | 4764 | striation$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 5 | BRS | 2 | ((438/629,636,637,639,640).CCLS.) and striation$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 6 | BRS | 144 | striation$1 and (438/$ 257/$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 7 | BRS | 0 | substrate with ((Si silicon) and (Ge germanium) and (gallium adj nitride gan "GaN" "Ga N")) and (striation$1 and (438/$ 257/$)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 8 | BRS | 8 | substrate with ((Si silicon) and (Ge germanium)) and (striation$1 and (438/$ 257/$)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 9 | BRS | 2 | striation$1 and (substrate$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 10 | BRS | 18 | substrate$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide and (cd critical adj dimension$2) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 11 | BRS | 197 | substrate$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 12 | BRS | 0 | substrate$1 with ((Si silicon) and (Ge germanium)) and DRAM and oxide | JPO |

|    | Time Stamp | Comments | Error Definition | Errors |
|----|------------|----------|------------------|--------|
| 1  | 2002/06/24 13:14 |  |  | 0 |
| 2  | 2002/06/24 13:48 |  |  | 0 |
| 3  | 2002/06/24 14:11 |  |  | 0 |
| 4  | 2002/06/24 13:54 |  |  | 0 |
| 5  | 2002/06/24 13:59 |  |  | 0 |
| 6  | 2002/06/24 14:06 |  |  | 0 |
| 7  | 2002/06/24 14:08 |  |  | 0 |
| 8  | 2002/06/24 14:09 |  |  | 0 |
| 9  | 2002/06/24 14:14 |  |  | 0 |
| 10 | 2002/06/24 14:18 |  |  | 0 |
| 11 | 2002/06/24 15:05 |  |  | 0 |
| 12 | 2002/06/24 14:29 |  |  | 0 |

|    | Type | Hits | Search Text | DBs |
|----|------|------|-------------|-----|
| 13 | BRS | 140 | substrate$1 with ((Si silicon)) and DRAM and oxide | JPO |
| 14 | BRS | 1 | substrate$1 with ((Si silicon)) and DRAM and oxide and (anti adj reflect$3 antireflect$3 Arc Arl) | JPO |
| 15 | BRS | 145 | substrate$1 with ((Si silicon)) and oxide and (anti adj reflect$3 antireflect$3 Arc Arl) | JPO |
| 16 | BRS | 2 | substrate$1 with ((Si silicon)) and oxide and (anti adj reflect$3 antireflect$3 Arc Arl) and (memory dynamic) | JPO |
| 17 | BRS | 18 | (substrate$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide) and (anti adj reflect$3 antireflect$3 Arc Arl) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 18 | BRS | 2 | striation$1 and (substrate$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

| | Time Stamp | Comments | Error Definition | Errors |
|---|---|---|---|---|
| 13 | 2002/06/24 14:29 | | | 0 |
| 14 | 2002/06/24 14:31 | | | 0 |
| 15 | 2002/06/24 14:31 | | | 0 |
| 16 | 2002/06/24 14:31 | | | 0 |
| 17 | 2002/06/24 17:07 | | | 0 |
| 18 | 2002/06/24 17:07 | | | 0 |